

5. (amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of claim 2, wherein there exists an oxidation induced stacking fault ring an inner diameter of which is 70% or less of an overall diameter, and in which there exists, surrounding the oxidation induced stacking fault ring, a defect free zone occupying 50% or more of a total surface area on one side.

B2 6. (amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of claim 2, wherein there exists an oxidation induced stacking fault ring an inner diameter of which is 50% or less of an overall diameter, and in which there exists, surrounding the oxidation induced stacking fault ring, a defect free zone occupying 75% or more of a total surface area on one side.

10. (amended) A silicon wafer for non-annealing, cut from a silicon ingot produced by the CZ method, wherein the silicon ingot is produced by pulling under a condition such that  $1.15 < G1_{edge}/VG1_{center} \leq 1.25$  an inner diameter of an oxidation induced stacking fault ring is at least  $1/2$  a wafer inner diameter.

B4 13. (amended) In a silicon wafer cut from a silicon ingot produced by the CZ method, a method to improve a gate oxide integrity in an area on the inside of an oxidation induced stacking fault ring by controlling a ratio of an oxidation induced stacking fault ring inner diameter to a crystal diameter,  $G1 \times G2$ , and  $G1_{edge}/G1_{center}$ .

☒ Please add new claim 14.

B5 14. The silicon wafer for non-annealing according to claim 10, wherein the silicon ingot has a density of void defects existing on the inside of an oxidation induced stacking fault ring reduced by expanding the inner diameter of the oxidation induced stacking fault.